

# Photoconductivity of CdS-CdSe granular films: experiment and theory

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We study experimentally the photoconductivity of CdS-CdSe granular films and reveal the connection between the film's microstructure and photoconductivity. The optimal time for heat-treatment of samples is found, for which the highest photoconductivity is achieved. Films of this type are characterized by compact packing of grains with large-area and narrow spacings between their edges. We suggest that the charge transfer occurs mostly through intergrain spacings, where electrons are trapped being released from grains by light quanta. These electrons first occupy energy levels in pores with low overlap of wave functions in different pores. As a result, the conductivity in this limit is low. Increasing the number of electrons leads to the occupation of higher energy levels, which correspond to states localized in narrow plane-like spaces between neighboring grains with good overlap of wave functions from different spacings. The conductivity in such a regime is high. A simple theoretical model is proposed.

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## I. INTRODUCTION

Materials with granular structure are widely used in modern electronics and radio engineering. These materials can be fabricated either by the traditional screen printing method known for a long time or by using new technologies, such as the direct forming of electronic devices by printers and opal crystals creation by concretion of spherical microparticles from water dredges. Modern technologies enable to fabricate much more pure and reproducible samples compared to the old ones. As a rule, by using these methods one obtains materials with granular or polycrystalline internal structure. Therefore, electronic and optical properties of granular semiconductors attract a lot of attention now. Semiconductors sometimes demonstrate anomalous electrophysical properties when they have a granular structure. One of the examples of such a material is a solid solution  $\text{CdSe}_{1-x}\text{CdS}_x$ , known as cadmium sulfoselenide. Photoresistors made from cadmium sulfoselenide are used in applications as photodetectors and optical couplers<sup>1,2,3,4,5,6,7</sup>. One of the characteristics of CdSe-CdS system, which is important for applications, is the ratio of the photocurrent and dark current<sup>8,9,10,11,12,13</sup>.

In the present paper, we study experimentally electrophysical parameters of CdSe-CdS solid solutions obtained by the screen printing method. We show that the ratios of the photocurrent and dark current for our samples are as high as  $10^4 - 10^7$ . We also found that our samples demonstrate negative temperature dependence of the conductivity, in a broad range of temperatures, that is a characteristic feature of metals. At the same time, CdSe-CdS crystals behave in a way, which is more typical for semiconductors and the ratio of photocurrent to the dark current is of the order of  $10^2 - 10^3$ , i.e., granularity favours high photosensitivity. We analyze the internal microstructure of CdSe-CdS films and reveal its connection to the ratio of the photocurrent and dark current. We found that there is some optimal time

for sample's heat-treatment during its fabrication, for which the photoconductivity is the highest. In such samples neighboring grains fit each other on large regions, which are almost flat and resemble crystal facets. At the same time, long time of agglomeration leads to the recrystallization of grains and disappearance of spaces between their facets. Short time of heat-treatment leads to wider gaps between grains and fitting between them is not so good. Thus, we assume that these spaces and their geometry can play an important role in the charge transfer process.

In the theoretical model, which is presented here, it is suggested that, during the illumination process, electrons jump from the interior of semiconductor grains into spaces between grains and the charge transfer occurs mostly through these spaces rather than by electrons tunnelling from grain to grain. In addition to the plane-like spacings between grains, there are also other cavities in the system, which are not so flat and which have a pore-like shape. Most of them are formed in regions where three grains fit each other. We suggest that the existence of two different types of cavities can be crucial for understanding of anomalously high values of the light-to-dark conductivity ratio. Due to the size quantization effects and Pauli principle, at first these electrons occupy energy levels which correspond to the states localized in pores. Because of the weak overlap of wave functions of electrons from different pores, the conductivity in such a regime is low. If the intensity of light becomes higher and the number of released electrons increases, they start to populate energy levels which correspond to the states localized in the plane-like spacings between grains. These states have higher energies compared to the ones corresponding to pores, as follows from simple quantum mechanical considerations. Wave functions of electrons from neighboring plane-like spaces overlap significantly and therefore conductivity in this regime is much higher than that in the previous one. It is important to note that the suggested scenario is in agreement with the negative temperature dependence of the photocurrent, which is typical for metals, not for semiconductors.

We also note that the similar anomalously high photosensitivity was found in another granular system, namely, polyxylene polymer (Parylene) films with semiconductor nanocrystals PbO and PbS. This material consists of polymer grains with characteristic sizes of several hundreds of nanometers, while PbO and PbS nanocrystals are located in spaces between these granules. The suggested here mechanism of charge transfer can also work in this system, with PbO and PbS nanocrystals serving as sources of electrons during the illumination and spaces between grains as a network for electrons transport.

The paper is organized as follows. In Section II, we describe our experimental results. Our theoretical model is presented in Section III. We conclude in Section IV.

## II. EXPERIMENT

We used CdS and CdSe powders as initial components in the paste. The powder of CdS-CdSe mixture is milled and particles of large sizes (more than 15  $\mu\text{m}$  in diameter) are sifted out using special sieves. Propylene glycol is used as a coupler. In order to get the paste, the prepared cadmium sulfoselenide powder and the coupler are mixed in a special barrel. Through a stencil, this paste is deposited on the ceramized substrate and then seasoned at room temperature for 0.5 hour. After that, samples are dried for 1 hour at temperature of 373 K. Finally, this raw material, which is represented by a film of 20-30  $\mu\text{m}$  thickness, is heat-treated in the stove with the free air access, then washed out and dried. More details on sample fabrication can be found in Ref.<sup>14</sup>.

The microstructure of obtained samples is studied using electron microscope. Typical pictures for  $\text{CdS}_{0.8}\text{Se}_{0.2}$  are

presented in Fig. 1. We found that the average grain size is around  $10 \mu m$ . Fig. 1(a) corresponds to the film which was heat-treated for 15 minutes at temperature  $T = 773 K$ ; Fig. 1(b) shows the structure of the film which was heated for a longer time, namely, 30 minutes and at higher temperature,  $T = 823 K$ ; Fig. 1(c) gives the image of the material which was heat-treated for 1 hour at  $T = 773 K$ . The analysis of images shows that the technology of film fabrication influences significantly the uniformity of grains distribution, their sizes, and what is very important, on the sinterness of intergrain boundaries. Increase of the time and temperature of sintering leads to recrystallization of grains and formation of sintered intergrain boundaries. One can see triple flat boundaries on Fig. 1(b). In fact, Fig. 1(b) corresponds to the intermediate case between totally recrystallized grains, which is obtained with long time of heat-treatment (60 minutes or more), and the material with relatively wide gaps between grains, shown in Fig. 1(a). As we show below, this intermediate regime with narrow spaces between grains favours higher values of photosensitivity. The material shown in Fig. 1(c) is characterized by disappearing intergrain spaces, many of them now look like grooves. Grains become larger due to the fact that individual particles merge during the heat-treatment.

The experimental setup used allows us to study film's electrophysical parameters by measuring its specific resistance by spreading resistance method. We used incandescent lamp as a source of light. By changing the distance between the lamp and the film and the strength of the current in the lamp we tuned the intensity of light illuminating the sample. We measure film's resistance, when the illumination ranges from 100 to 1500 lux. We found that, in addition to the sample microstructure, the photoresistance depends also on the selenium concentration  $x$ . Absence of selenium results in the lower photoresistance. The dark resistance of all the samples is larger than  $10^9 \text{ Ohm}$ . The ratio of the photocurrent and dark current for these films is  $10^4$ - $10^6$ . For several samples, this ratio is even higher, of the order of  $10^7$ . Such high values of photosensitivity were also reported in Refs.<sup>8,9,10,12</sup>. The dependence of the resistance on illumination is shown in Fig. 2 for  $\text{CdS}_{0.8}\text{Se}_{0.2}$  for two different samples. The first one was heat-treated for the intermediate time (30 minutes), while the second one – for long time (60 minutes). We found that the lowest photoresistance is achieved for samples, which were heat-treated for an intermediate time and which are therefore characterized by good fitting of intergranular boundaries, but without their recrystallization. Note that the measured photoresistance of films, which were heat-treated for only several minutes, was even higher than that corresponding to curve 2 in Fig. 2. The optimal time for heat-treatment was found to be around 30 minutes. The existence of the optimal time for heat-treatment for CdSe thin films obtained by the chemical bath deposition technique was also reported in Ref.<sup>12</sup>.

We also study temperature dependences of photoconductivity at constant illumination, 200 lux. Measurements were conducted for temperature range from 338 to 422 K. Our results for  $\text{CdS}_{0.8}\text{Se}_{0.2}$  are presented in Fig. 3, where we again plot curves for the samples, which were heat-treated for different times. One can see the tendency for maximum specific resistance to decrease with the increase of the time and temperature of heat-treatment. Also, note that the positive temperature dependence of resistance is not typical for semiconductors, but is traditional for metals. These facts are important for our theoretical model, which is presented in the next Section. Such unusual temperature dependence of photoresistance was also reported in Refs.<sup>8,10</sup>. However, it was detected in much more narrow range of temperatures. In Refs.<sup>9,13</sup> temperature dependence of photoresistance is usual, i.e., positive.

### III. THEORETICAL MODEL

We consider here samples prepared with an intermediate time of heat-treatment. Such samples, consisting of a large amount of small grains, have some cavities between grains. Free electrons are generated inside grains during an illumination process and then they can be trapped in these spaces. The backward jumps of electrons from intergrain spaces inside grains are suppressed due to the fact that such processes cost a certain amount of energy. Thus, the system of spaces between individual grains forms a three-dimensional potential well with complicated topology, which can serve as a network for the electron motion through the system. Our approach is based on the assumption that the size quantization effect within intergrain cavities can play an important role in the mechanism of a high light-to-dark conductivity ratio. The network of cavities contains two main types of segments. Blocks of the first type are positioned between two facets of neighboring grains. They have a quasi-two-dimensional geometry with typical thickness of few nanometers and lateral dimensions of hundreds of nanometers, as can be seen in Fig. 1. Spaces of the second type are situated in regions where three (or sometimes more) grains fit each other. Such pores have an elongated shape with the height of the order of 100 nm and lateral dimensions of tens of nanometers. They are situated mostly between edges of plane-like wells and separate them from each other. It is important to emphasize that photoconductivity depends strongly on the way the material is fabricated. The better a fitting between facets of grains and the denser their packing, the higher the photoconductivity. At the same time, total recrystallization of grains and disappearance of narrow gaps between them decreases the photoconductivity. In other words, by approaching the internal constitution of the sample to the (quasi)regular structure with simultaneous keeping of gaps between grains, one can increase a conductivity. This shows that the order in positions of individual potential wells plays an important role in the process of electron transfer through the system, so that these wells, as we suggest, are a crucial ingredient of the electron conduction mechanism.

Due to the size quantization, one-electron levels in the pore-like potential wells are characterized, in average, by much lower energy compared to the levels for the narrow plane-like wells. At the same time, wave functions of the electrons confined in the plane-like wells have much larger spacial extension due to the large area of flat spaces between edges of grains. Due to geometrical reasons, wave functions of the electrons from two adjacent plane-like wells overlap significantly, whereas wave functions of electrons in pores are much strongly localized. The difference between the geometry of the two potential wells thus results in the dramatic difference between the effective masses of electrons localized within the two types of wells: the one for the pore-like well is much larger than the one for the plane-like well. This implies that values of conductivity due to the two types of electrons can be very different from each other. Since electrons obey Fermi statistics, two of them cannot occupy the same level. Therefore, gradual increase of the number of electrons in the intergrain network of spacings leads, at first, to the occupation of the states in pores, which have lower energy and more localized wave functions. As a result, the conductivity in this regime is low. By increasing a number of electrons in the system, we fill one-electron levels localized in planes between grains and conductivity grows rapidly.

Since the photocurrent is quite sensitive to the order in individual grains positions, it is reasonable to consider theoretically the situation, when the system is so close to the regular one that randomness can be treated perturbatively. Of course, it is difficult to approach this regime experimentally, but such an analysis allows one to reveal, at least on a qualitative level, the role of two different potential wells in the process of a charge transfer. Physically it corre-

sponds to the "ideal" situation, when all the grains are identical and packed compactly. Note that fast technological progress makes this picture not so unrealistic. Within this approach, for the description of conductivity through the pore states, we can use the approximation of strongly-localized electrons, and for the conductivity through the plane states, we can apply the approximation of almost free electrons. In our model, the positive (metallic) temperature dependence of resistance, found experimentally, is natural, because, from the quantum mechanical point of view, the periodic potential can favour a metallic type of conductivity.

Let us consider first the conductivity through pore states, at low temperatures. We assume that irregularity in pores positions is relatively low and we estimate an effective mass for electrons in such a system. Shrodinger equation for the electron in the *isolated* pore reads

$$-\frac{\hbar^2}{2m}\Delta\psi_0 + U(\mathbf{r})\psi_0 = \varepsilon_0\psi_0, \quad (1)$$

where  $\psi_0$  and  $\varepsilon_0$  are the electron wave function and energy,  $U(\mathbf{r})$  is the potential energy. Zero-order approximation wave function for regular system of pores is given by

$$\psi^{(0)}(\mathbf{r}) = \sum_n e^{i\mathbf{k}\mathbf{r}_n} \psi_0(\mathbf{r} - \mathbf{r}_n), \quad (2)$$

where  $\mathbf{r}_n$  stands for pores positions and  $\mathbf{k}$  is a wave vector. We also introduce an exact one-electron wave function  $\psi(\mathbf{r})$ , which is defined through the Shrodinger equation for the electron in the *periodic* potential:

$$-\frac{\hbar^2}{2m}\Delta\psi + V(\mathbf{r})\psi = \varepsilon\psi, \quad (3)$$

where  $V(\mathbf{r})$  is a Hartree-Fock potential. From Eq. (3) we find

$$\varepsilon = \frac{\int d\mathbf{r} \psi^* \left( -\frac{\hbar^2}{2m}\Delta + V(\mathbf{r}) \right) \psi}{\int d\mathbf{r} \psi^* \psi}. \quad (4)$$

As an approximation for  $\psi(\mathbf{r})$ , we use  $\psi^{(0)}(\mathbf{r})$ . Taking into account Eq. (1) we rewrite Eq. (4) as

$$\varepsilon = \varepsilon_0 + \frac{\int d\mathbf{r} \sum_n e^{i\mathbf{k}\mathbf{r}_n} \psi_0(\mathbf{r} - \mathbf{r}_n) \psi_0^*(\mathbf{r}) (V(\mathbf{r}) - U(\mathbf{r} - \mathbf{r}_n))}{\int d\mathbf{r} \sum_n e^{i\mathbf{k}\mathbf{r}_n} \psi_0(\mathbf{r} - \mathbf{r}_n) \psi_0^*(\mathbf{r})}. \quad (5)$$

Now we assume that electron wave functions from different pores do not overlap:

$$\int d\mathbf{r} \psi_0(\mathbf{r} - \mathbf{r}_n) \psi_0^*(\mathbf{r}) = \delta_{0n}. \quad (6)$$

Under this assumption, Eq. (5) can be presented as

$$\varepsilon = \varepsilon_0 - \Delta - \sum_{n \neq 0} e^{i\mathbf{k}\mathbf{r}_n} E_n, \quad (7)$$

where

$$\Delta = - \int d\mathbf{r} \psi_0(\mathbf{r}) \psi_0^*(\mathbf{r}) (V(\mathbf{r}) - U(\mathbf{r})), \quad (8)$$

$$E_{n \neq 0} = - \int d\mathbf{r} \psi_0(\mathbf{r} - \mathbf{r}_n) \psi_0^*(\mathbf{r}) (V(\mathbf{r}) - U(\mathbf{r} - \mathbf{r}_n)). \quad (9)$$

Eq. (7) determines the difference between the electron energy in isolated pore  $\varepsilon_0$  from that in the regular system of pores:  $\Delta$  is just an additive constant, but the sum in the RHS of Eq. (7) depends on the wave vector  $\mathbf{k}$  and this term is responsible for the electron effective mass.

For simplicity, we now assume that pores are spherically symmetric and positioned in a cubic lattice with period  $a$ . These assumptions do not influence our main conclusions. We also take into account only nearest neighbors and obtain

$$\varepsilon = \varepsilon_0 - \Delta - E_1 (e^{ik_x a} + e^{-ik_x a} + e^{-ik_y a} + e^{ik_y a}) = \varepsilon_0 - \Delta - 2E_1 (\cos k_x a + \cos k_y a). \quad (10)$$

At small values of wave vector, Eq. (10) reads

$$\varepsilon \simeq \varepsilon_0 - \Delta - 2E_1 \left( 2 - \frac{a^2}{2} (k_x^2 + k_y^2) \right). \quad (11)$$

From Eq. (11) it is straightforward to find the electron effective mass

$$m^* = \frac{\hbar^2}{\partial^2 \varepsilon / \partial k^2} = \frac{\hbar^2}{2E_1 a^2}. \quad (12)$$

Eq. (12) shows that the effective mass depends on  $E_1$  which is very sensitive to the overlap of wave functions from two neighboring pores. Since the overlap is small, the effective mass is much larger than the free electron mass.

We now consider an opposite situation, when the electron is confined in the plane-like space between grains facets. Since such a spacing has a flat geometry with the thickness much smaller than lateral dimensions, we first discuss the case of an infinite layer, where electrons motion in the perpendicular direction  $x$  is restricted by energy barrier  $U_0 \sim 5$  eV and the layer width  $b$  along  $x$  is  $\sim 1 \div 10$  nm. It is easy to see that the characteristic energy  $\hbar^2/2mb^2$  is much larger than  $U_0$ , i.e., the well is shallow. The electron wave function in such an infinite layer can be written as

$$\psi^{(l)}(\mathbf{r}) = f(x)e^{i(k_y y + k_z z)}, \quad (13)$$

whereas the Shrodinger equation in the  $x$  direction reads

$$-\frac{\hbar^2}{2m} \frac{d^2 f}{dx^2} + f \left[ U(x) + \frac{\hbar^2}{2m} (k_y^2 + k_z^2) \right] = E^{(l)} f. \quad (14)$$

From Eq. (14) we can conclude that the problem is reduced to the one-dimensional one, provided that the potential energy profile is lifted by an amount of  $\hbar^2 (k_y^2 + k_z^2) / 2m$ , as a whole. So that we have a shallow potential well, which has always an energy level situated near its top. Due to the motion in  $y$  and  $z$  directions, in finite layer, the total number of electron states is finite, but large. If we now consider a periodic in space system of large finite layers separated by small pores, we immediately see that the electron effective mass  $m^*$  along the layer should be rather small, i.e., close to the electron physical mass  $m$ , as usual in the approximation of almost free electrons.

The conductivity  $\sigma$  can be estimated using a well-known Drude formula:

$$\sigma = \frac{ne^2\tau}{m^*}, \quad (15)$$

where  $\tau$  is the free flight time. From this formula we see that  $\sigma$  depends strongly on the electron effective mass. As we show, the effective mass for the electrons in the pore states is much larger than that for plane-like delocalized states. Therefore, we expect that the conductivity through the pore states is much smaller.

Note that we are concentrated on the model, in which the system is close to the periodic one. In more realistic treatments, extremely high photoconductivity can be explained in terms of Anderson localization. Pore localized states are characterized by lower energy and they are filled by electrons first of all. Delocalized states in spaces between crystals facets are filled after that giving rise to high photoconductivity.

#### IV. CONCLUSIONS

We studied both experimentally and theoretically electrophysical properties of granular CdS-CdSe (cadmium sulfoselenide) films. This material is very sensitive to the illumination by light: the ratio of the photocurrent and dark current can be of the order of  $10^7$ . In addition, the temperature dependence of specific resistance is positive. Such a behaviour is unusual for semiconductors, but is typical for metals. Using electron microscope, we analyzed films microstructure and we showed that a long time of heat-treatment of samples during their fabrication leads to more compact packing of grains and better fitting between grains boundaries. We revealed the link between the photoconductivity and the microstructure of the films. Films with more ordered structure demonstrate higher photosensitivity. At the same time, materials, which were heat-treated for rather long time (60 minutes or more), have recrystallized intergrain boundaries with no clear gaps between grains. Such films are characterized by lower photosensitivity. So that, there is an optimal time for heat-treatment, which leads to compact packing of grains but without their total recrystallization and with keeping gaps between their edges. Based on this fact, we suggested a theoretical explanation for the extremely high values of photoconductivity. In our model, electrons jump from the internal parts of grains to the intergrain spaces, during the process of illumination. These electrons then become trapped in the intergrain spaces. We argue that there are essentially two types of cavities in the system. The first one is represented by large-area narrow spacings between two neighbouring grains, these spaces being nearly flat. Cavities of the second type can be found in places, where three grains fit each other. Their shape is more three-dimensional and sizes are much larger than the typical width of intergrain plane-like spacings. Due to the size quantization, potential wells of the second type have lower energy levels compared to the potential well of the first type. Therefore, under the light illumination, electrons, which are fermions, first occupy levels in pores, and only after that they start to fill levels in plane-like spacings between grains. Wave functions of electrons in pores are much more localized in space compared to electrons wave functions in spaces between grains, and therefore we expect that the conductivity in this regime is much lower. We considered theoretically the "idealized" situation, when the film structure is so close to the regular one that randomness can be treated perturbatively, and the band theory is applicable. Of course, such a regime can hardly be achieved experimentally, but our analysis allowed us to reveal the effect of two types of intergrain cavities on the resistance. We showed that the effective mass for electrons localized in pores should be much larger than that for electrons in the plane-like spaces between neighbouring spaces, and therefore the photoconductivity depends dramatically on the number of electrons trapped between grains, i.e., on the illumination.

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## VI. FIGURE CAPTIONS

**Fig. 1.** Micrographs of granular  $\text{CdS}_{0.8}\text{Se}_{0.2}$  films fabricated with different times of heat-treatment.

**Fig. 2.** The measured dependences of specific resistance of  $\text{CdS}_{0.8}\text{Se}_{0.2}$  films on the illumination. Curves 1 and 2 correspond to samples which were heat-treated for 30 and 60 minutes, respectively.

**Fig. 3.** The measured temperature dependences of specific resistance of  $\text{CdS}_{0.8}\text{Se}_{0.2}$  films. Curves 1 and 2 correspond to samples which were heat-treated for 15 and 30 minutes, respectively.

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